- Floating Bootstrap or Ground-Reference High-Side Driver
- Adaptive Dead-Time Control
- 50-ns Max Rise/Fall Times With 3.3-nF Load
- 2.4-A Typical Output Current
- 4.5-V to 15-V Supply Voltage Range
- TTL-Compatible Inputs
- Internal Schottky Bootstrap Diode
- Low Supply Current....3 mA Typical
- Ideal for High-Current Single or Multiphase Power Supplies
- 40°C to 125°C Operating Virtual Junction-Temperature Range

description

The TPS2836 and TPS2837 are MOSFET drivers for synchronous-buck power stages. These devices are ideal for designing a high-performance power supply using switching controllers that do not have MOSFET drivers. The drivers are designed to deliver minimum 2-A peak currents into large capacitive loads. The high-side driver can be configured as ground-reference or as floating-bootstrap. An adaptive dead-time control circuit eliminates shoot-through currents through the main power FETs during switching transitions and provides high efficiency for the buck regulator.

The TPS2836 has a noninverting input, while the TPS2837 has an inverting input. These drivers, available in 8-terminal SOIC packages, operate over a junction temperature range of – 40°C to 125°C.

AVAILABLE OPTIONS

	PACKAGED DEVICES
TJ	SOIC (D)
– 40°C to 125°C	TPS2836D TPS2837D

The D package is available taped and reeled. Add R suffix to device type (e.g., TPS2836DR)

Related Synchronous MOS FET Drivers

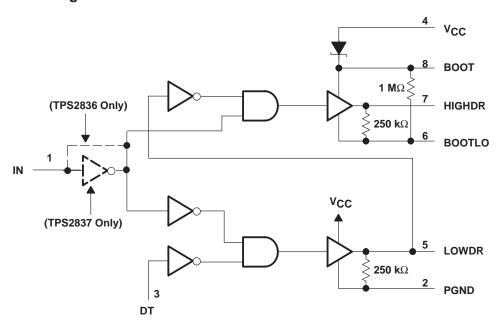
DEVICE NAME	ADDITIONAL FEATURES	INPUTS		
TPS2830	ENABLE CYNIC and CROMBAR	CMOS	Noninverted	
TPS2831	ENABLE, SYNC and CROWBAR	CMOS	Inverted	
TPS2832	W/O ENABLE OVALO LODOVADAD	01400	Noninverted	
TPS2833	W/O ENABLE, SYNC and CROWBAR	CMOS	Inverted	
TPS2834			Noninverted	
TPS2835	ENABLE, SYNC and CROWBAR	TTL	Inverted	



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



functional block diagram



Terminal Functions

TERMINAL			DECORIDEION
NAME	NO.	1/0	DESCRIPTION
BOOT 8		I	Bootstrap terminal. A ceramic capacitor is connected between BOOT and BOOTLO to develop the floating bootstrap voltage for the high-side MOSFET. The capacitor value is typically between 0.1 μ F and 1 μ F.
BOOTLO 6 O		0	This terminal connects to the junction of the high-side and low-side MOSFETs.
DT	3	- 1	Dead-time control terminal. Connect DT to the junction of the high-side and low-side MOSFETs
HIGHDR	7	0	Output drive for the high-side power MOSFET
IN	1	Ţ	Input signal to the MOSFET drivers (noninverting input for the TPS2836; inverting input for the TPS2837).
LOWDR	5	0	Output drive for the low-side power MOSFET
PGND	2		Power ground. Connect to the FET power ground.
Vcc	4	I	Input supply. Recommended that a 1 μF capacitor be connected from V _{CC} to PGND.



detailed description

low-side driver

The low-side driver is designed to drive low $r_{DS(on)}$ N-channel MOSFETs. The current rating of the driver is 2 A, source and sink.

high-side driver

The high-side driver is designed to drive low $r_{DS(on)}$ N-channel MOSFETs. The current rating of the driver is 2 A, source and sink. The high-side driver can be configured as a ground-reference driver or a floating bootstrap driver. The internal bootstrap diode is a Schottky for improved drive efficiency. The maximum voltage that can be applied between the BOOT terminal and ground is 30 V.

dead-time (DT) control

Dead-time control prevents shoot-through current from flowing through the main power FETs during switching transitions by controlling the turnon times of the MOSFET drivers. The high-side driver is not allowed to turn on until the gate drive voltage to the low-side FET is low, and the low-side driver is not allowed to turn on until the voltage at the junction of the power FETs (Vdrain) is low; the TTL-compatible DT terminal connects to the junction of the power FETs.

IN

The IN terminal is a TTL-compatible digital terminal that is the input control signal for the drivers. The TPS2836 has a noninverting input; the TPS2837 has an inverting input.

absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage range, V _{CC} (see Note 1)	0.3 V to 16 V
Input voltage range: BOOT to PGND (high-side driver ON)	
BOOTLO to PGND	
BOOT to BOOTLO	
IN	
DT	
Continuous total power dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T _J	–40°C to 125°C
Storage temperature range, T _{Stq}	–65°C to 150°C
Lead temperature soldering 1,6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{\scriptsize A}} \le 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
D	600 mW	6.0 mW/°C	330 mW	240 mW

recommended operating conditions

		М	IIN NOM	MAX	UNIT
Supply voltage	VCC	4	4.5	15	V
Input voltage	BOOT to PGND	4	4.5	28	V



NOTE 1: Unless otherwise specified, all voltages are with respect to PGND.

TPS2836, TPS2837 SYNCHRONOUS-BUCK MOSFET DRIVER WITH DEAD-TIME CONTROL

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electrical characteristics over recommended operating virtual junction temperature range, $V_{CC} = 6.5 \text{ V}$, $C_L = 3.3 \text{ nF}$ (unless otherwise noted)

supply current

	PARAMETER	TEST CO	MIN	TYP	MAX	UNIT	
	Supply voltage range			4.5		15	V
	Quiescent current	V _{CC} =15 V,	V(ENABLE) = LOW			100	^
vcc	Quiescent current	V _{CC} =15 V,	V _(ENABLE) = HIGH		300	400	μΑ
	Quiescent current	V _{CC} =12 V, f _{SWX} = 200 kHz, C _{HIGHDR} = 50 pF,	BOOTLO grounded, CLOWDR = 50 pF, See Note 2		3		mA

NOTE 2: Ensured by design, not production tested.

output drivers

PARAMETER		TEST CONDIT	TONS	MIN	TYP	MAX	UNIT		
		Duty cycle < 2%,	VBOOT - VBOOTLO = 4.5 V	VHIGHDR = 4 V	0.7	1.1			
	High-side sink (see Note 4)	t _{pw} < 100 μs	VBOOT - VBOOTLO = 6.5 V, VHIGHDR = 5 V			1.5		Α	
	(666 11616 1)	(see Note 3)	V _{BOOT} – V _{BOOTLO} = 12 V,	VHIGHDR = 10.5 V	2	2.4			
	High-side	Duty cycle < 2%,	$V_{BOOT} - V_{BOOTLO} = 4.5 V_{BOOTLO}$	V _{HIGHDR} = 0.5V	1.2	1.4			
	source	t _{pw} < 100 μs	$V_{BOOT} - V_{BOOTLO} = 6.5 V_{BOOTLO}$	V _{HIGHDR} = 1.5 V	1.3	1.6		Α	
Peak output-	(see Note 4)	(see Note 3)	$V_{BOOT} - V_{BOOTLO} = 12 V$	VHIGHDR = 1.5 V	2.3	2.7			
current	I am at da at at	Duty cycle < 2%,	$V_{CC} = 4.5 \text{ V},$	V _{LOWDR} = 4 V	1.3	1.8			
	Low-side sink (see Note 4)	t _{pw} < 100 μs	$V_{CC} = 6.5 \text{ V},$	V _{LOWDR} = 5 V	2	2.5		Α	
	(666 11616 1)	(see Note 3)	V _{CC} = 12 V,	V _{LOWDR} = 10.5 V	3	3.5			
	Low-side source (see Note 4)	Duty cycle < 2%, t _{pw} < 100 µs (see Note 3)	$V_{CC} = 4.5 \text{ V},$	$V_{LOWDR} = 0.5V$	1.4	1.7			
			$V_{CC} = 6.5 \text{ V},$	V _{LOWDR} = 1.5 V	2	2.4		Α	
			V _{CC} = 12 V,	$V_{LOWDR} = 1.5 V$	2.5	3			
			$V_{BOOT} - V_{BOOTLO} = 4.5 V_{BOOTLO}$	V _{HIGHDR} = 0.5 V			5		
	High-side sink (see Note 4)		$V_{BOOT} - V_{BOOTLO} = 6.5 V_{BOOTLO}$	VHIGHDR = 0.5 V			5	Ω	
			VBOOT - VBOOTLO = 12 V, VHIGHDR = 0.5 V				5		
			VBOOT - VBOOTLO = 4.5 V	VHIGHDR = 4 V			75		
	High-side source	e (see Note 4)	$V_{BOOT} - V_{BOOTLO} = 6.5 V_{BOOTLO}$	VHIGHDR = 6 V			75	Ω	
Output			$V_{BOOT} - V_{BOOTLO} = 12 V$	VHIGHDR =11.5 V			75		
resistance			$V_{DRV} = 4.5 V,$	$V_{LOWDR} = 0.5 V$			9		
	Low-side sink (s	ee Note 4)	V _{DRV} = 6.5 V	$V_{LOWDR} = 0.5 V$			7.5	Ω	
			V _{DRV} = 12 V,	$V_{LOWDR} = 0.5 V$			6		
			V _{DRV} = 4.5 V,	V _{LOWDR} = 4 V			75		
	Low-side source	(see Note 4)	V _{DRV} = 6.5 V,	V _{LOWDR} = 6 V			75	Ω	
			$V_{DRV} = 12 V$	V _{LOWDR} = 11.5 V			75		

NOTES: 3. Ensured by design, not production tested.

4. The pullup/pulldown circuits of the drivers are bipolar and MOSFET transistors in parallel. The peak output current rating is the combined current from the bipolar and MOSFET transistors. The output resistance is the r_{DS(on)} of the MOSFET transistor when the voltage on the driver output is less than the saturation voltage of the bipolar transistor.



electrical characteristics over recommended operating virtual junction temperature range, V_{CC} = 6.5 V, C_L = 3.3 nF (unless otherwise noted) (continued)

dead-time

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{IH}	High-level input voltage	LOWIDD	Overathe V and and Alexa Nets (2)	0.7V _{CC}			V
V_{IL}	Low-level input voltage	LOWDR	Over the V _{CC} range (see Note 3)			1	V
VIH	High-level input voltage	DT	Over the Vele range	2		·	V
V_{IL}	Low-level input voltage	וטו	Over the V _{CC} range			1	V

NOTE 3: Ensured by design, not production tested.

digital control terminals (IN)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{IH}	High-level input voltage	Over the Valarange	2			V
VIL	Low-level input voltage	Over the V _{CC} range			1	V

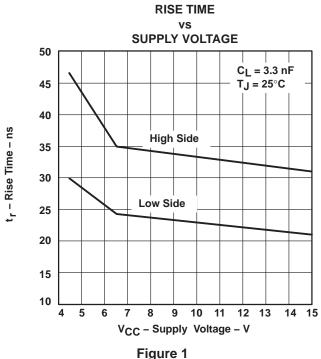
switching characteristics over recommended operating virtual junction temperature range, C_L = 3.3 nF (unless otherwise noted)

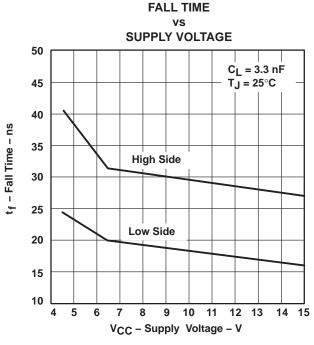
F	PARAMETER	TEST CO	MIN	TYP	MAX	UNIT		
		$V_{BOOT} = 4.5 V$	VBOOTLO = 0 V			60		
	HIGHDR output (see Note 3)	$V_{BOOT} = 6.5 V$	V _{BOOTLO} = 0 V			50	ns	
Dies time		V _{BOOT} = 12 V,	V _{BOOTLO} = 0 V			50		
Rise time		V _{CC} = 4.5 V				40		
	LOWDR output (see Note 3)	V _{CC} = 6.5 V				30	ns	
		V _{CC} = 12 V				30		
		$V_{BOOT} = 4.5 V,$	V _{BOOTLO} = 0 V			50		
	HIGHDR output (see Note 3)	$V_{BOOT} = 6.5 \text{ V},$	V _{BOOTLO} = 0 V			40	ns	
Fall time		$V_{BOOT} = 12 V$,	V _{BOOTLO} = 0 V			40		
rali ume		V _{CC} = 4.5 V				40		
	LOWDR output (see Note 3)	V _{CC} = 6.5 V			30	ns		
		V _{CC} = 12 V				30		
	LHOURD as it as less (so about a set of	$V_{BOOT} = 4.5 V,$	V _{BOOTLO} = 0 V			95		
	HIGHDR going low (excluding dead- time) (see Note 3)	$V_{BOOT} = 6.5 V,$	V _{BOOTLO} = 0 V			80	ns	
Propagation delay time		$V_{BOOT} = 12 V$	V _{BOOTLO} = 0 V			65		
Propagation delay time	LOWDD spins high (avaluation	$V_{BOOT} = 4.5 V$	V _{BOOTLO} = 0 V			80		
	LOWDR going high (excluding dead-time) (see Note 3)	$V_{BOOT} = 6.5 V$	V _{BOOTLO} = 0 V			70	ns	
		$V_{BOOT} = 12 V$	V _{BOOTLO} = 0 V			60		
	LOWD and an law (and but a stand	V _{CC} = 4.5 V				80		
Propagation delay time	LOWDR going low (excluding dead- time) (see Note 3)	V _{CC} = 6.5 V				70	ns	
		V _{CC} = 12 V				60		
	DT to LOWDD and LOWDD to	V _{CC} = 4.5 V		40		170		
Driver nonoverlap time	DT to LOWDR and LOWDR to HIGHDR (see Note 3)	V _{CC} = 6.5 V		25		135	ns	
		V _{CC} = 12 V		15		85		

NOTE 3: Ensured by design, not production tested.

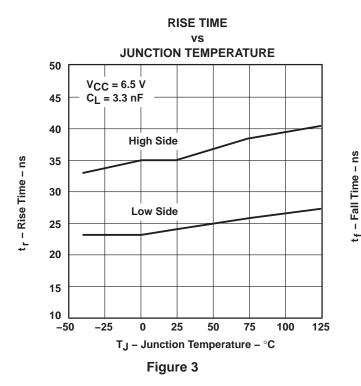


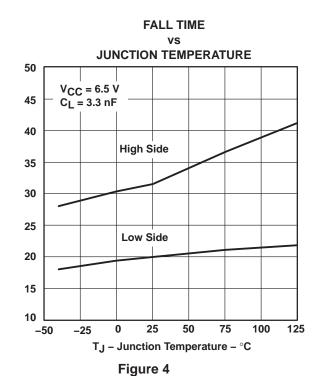
TYPICAL CHARACTERISTICS











HIGH-TO-LOW PROPAGATION DELAY TIME

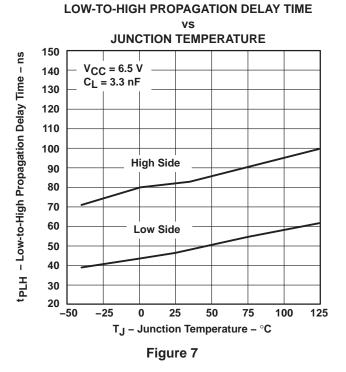
TYPICAL CHARACTERISTICS

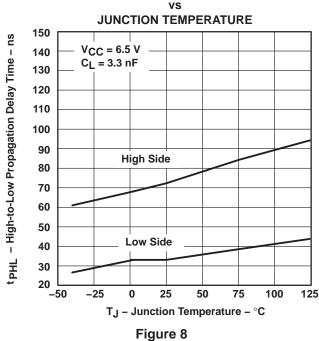
LOW-TO-HIGH PROPAGATION DELAY TIME SUPPLY VOLTAGE, LOW TO HIGH LEVEL tpLH - Low-to-High Propagation Delay Time - ns C_L = 3.3 nF T_J = 25°C Low Side V_{CC} - Supply Voltage - V

Figure 5

SUPPLY VOLTAGE, HIGH TO LOW LEVEL tPHL - High-to-Low Propagation Delay Time - ns $C_{L} = 3.3 \text{ nF}$ $T_J^- = 25^{\circ}C$ **High Side** Low Side V_{CC} - Supply Voltage - V Figure 6

HIGH-TO-LOW PROPAGATION DELAY TIME





TYPICAL CHARACTERISTICS

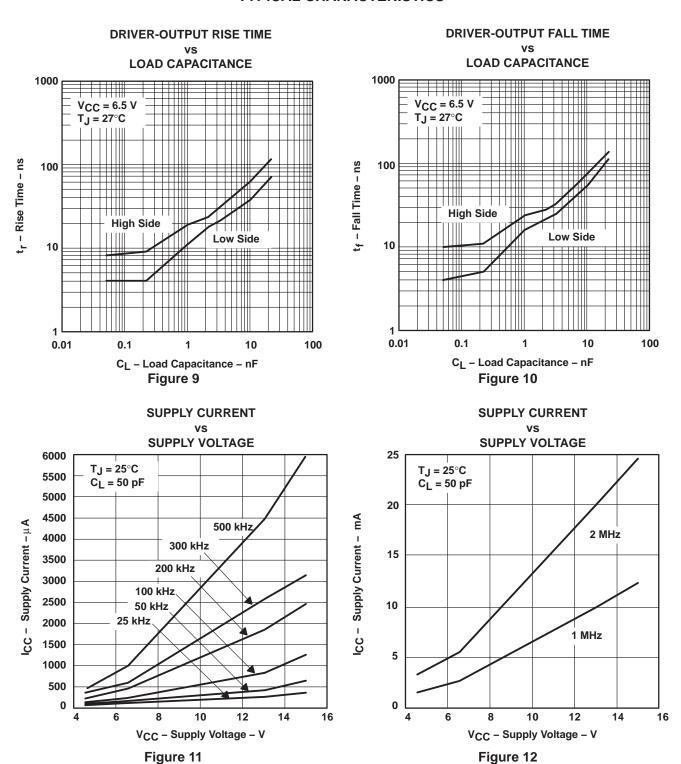




Figure 16

TYPICAL CHARACTERISTICS

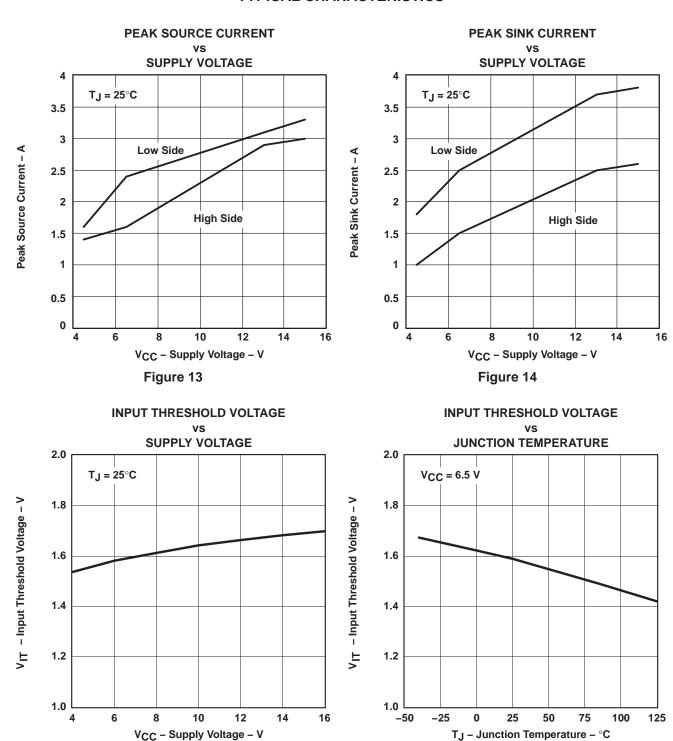




Figure 15

APPLICATION INFORMATION

Figure 17 shows the circuit schematic of a 100-kHz synchronous-buck converter implemented with a TL5001A pulse-width-modulation (PWM) controller and a TPS2837 driver. The converter operates over an input range from 4.5 V to 12 V and has a 3.3-V output. The circuit can supply 3 A continuous load and the transient load is 5 A. The converter achieves an efficiency of 94% for $V_{IN} = 5 \text{ V}$, $I_{load} = 1 \text{ A}$, and 93% for $V_{IN} = 5 \text{ V}$, $I_{load} = 3 \text{ A}$.

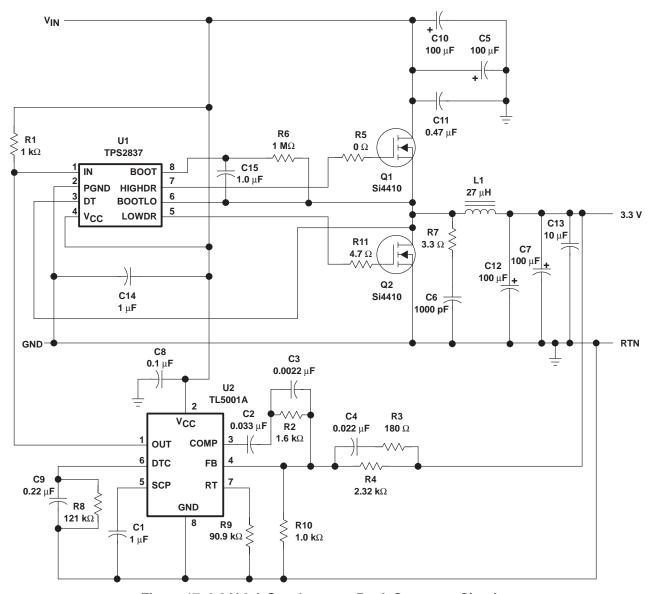


Figure 17. 3.3 V 3 A Synchronous-Buck Converter Circuit



TPS2836, TPS2837 SYNCHRONOUS-BUCK MOSFET DRIVER WITH DEAD-TIME CONTROL

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APPLICATION INFORMATION

Great care should be taken when laying out the PC board. The power-processing section is the most critical and will generate large amounts of EMI if not properly configured. The junction of Q1, Q2, and L1 should be very tight. The connection from Q1 drain to the positive sides of C5, C10, and C11 and the connection from Q2 source to the negative sides of C5, C10, and C11 should be as short as possible. The negative terminals of C7 and C12 should also be connected to Q2 source.

Next, the traces from the MOSFET driver to the power switches should be considered. The BOOTLO signal from the junction of Q1 and Q2 carries the large gate drive current pulses and should be as heavy as the gate drive traces. The bypass capacitor (C14) should be tied directly across V_{CC} and PGND.

The next most sensitive node is the FB node on the controller (terminal 4 on the TL5001A). This node is very sensitive to noise pickup and should be isolated from the high-current power stage and be as short as possible. The ground around the controller and low-level circuitry should be tied to the power ground as the output. If these three areas are properly laid out, the rest of the circuit should not have other EMI problems and the power supply will be relatively free of noise.

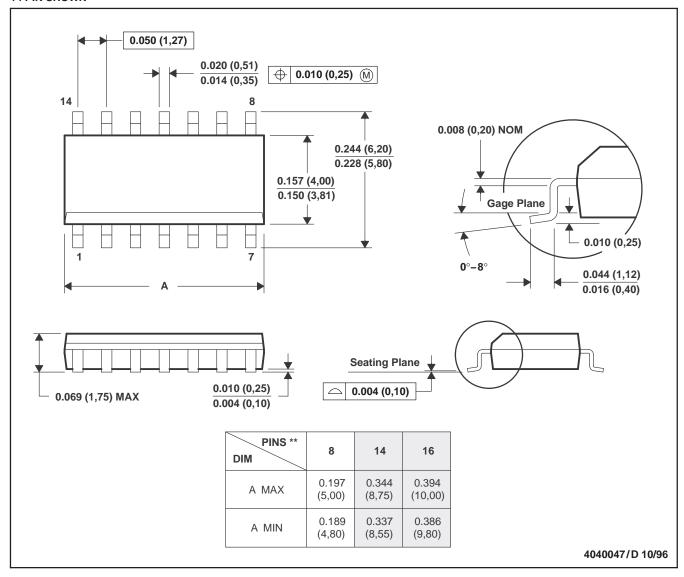


MECHANICAL DATA

D (R-PDSO-G**)

14 PIN SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-012



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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3) Ball material		Peak reflow		(6)
						(4)	(5)		
TPS2836D	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	-40 to 125	2836
TPS2836DR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2836
TPS2836DR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2836
TPS2837D	Obsolete	Production	SOIC (D) 8	-	-	Call TI	Call TI	-40 to 125	2837
TPS2837DR	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2837
TPS2837DR.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	2837

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



PACKAGE OPTION ADDENDUM

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

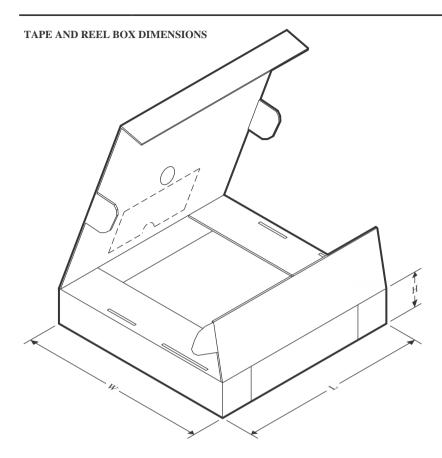


*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS2836DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TPS2837DR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS2836DR	SOIC	D	8	2500	340.5	338.1	20.6
TPS2837DR	SOIC	D	8	2500	353.0	353.0	32.0

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